

said at least one metal contact;

B¹

a second insulator layer overlying said at least first one metal pad; and,

at least one solder contact formed in the second insulator and in contact with said at least one metal pad, said solder contact having a diameter less than 100 microns.

71. (Twice amended) A semiconductor device formed on a semiconductor substrate having at least one metal contact formed thereon, said semiconductor device comprising:

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a first insulator layer overlying said at least one metal contact;

at least one metal pad overlying said first insulator layer and in contact with said at least one metal contact;

a second insulator layer overlying said at least first one metal pad; and

at least one solder contact formed in the second insulator and in contact with said at least one metal pad, said solder contact having a diameter between 2 and 100 microns.

Please add claims 74-75:

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74: The semiconductor device of claim 40 wherein the solder contacts have a diameter less than 50 microns.

75. The semiconductor device of claim 40 wherein the solder contacts have a diameter less than 25 microns.
